









**CSD19536KCS** SLPS485C - JANUARY 2014 - REVISED MAY 2024

# **CSD19536KCS 100V N-Channel NexFET™ Power MOSFET**

### 1 Features

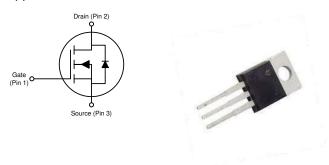
- Ultra-low  $Q_g$  and  $Q_{gd}$  Low thermal resistance
- Avalanche rated
- Pb-Free terminal plating
- RoHS compliant
- Halogen free
- TO-220 plastic package

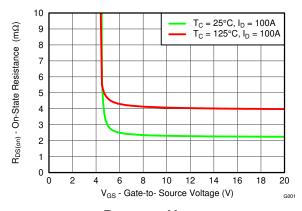
### 2 Applications

- Secondary side synchronous rectifier
- Motor control

## 3 Description

This 100V, 2.3mΩ, TO-220 NexFET<sup>™</sup> power MOSFET is designed to minimize losses in power conversion applications.





R<sub>DS(on)</sub> vs V<sub>GS</sub>

#### **Product Summary**

T <sub>A</sub> = 25°	C	TYPICAL VA	UNIT	
V <sub>DS</sub>	Drain-to-Source Voltage 100		V	
Qg	Gate Charge Total (10V)	118		
Q <sub>gd</sub>	Gate Charge Gate to Drain	17		nC
В	Drain-to-Source On-Resistance	V <sub>GS</sub> = 6V	2.5	mΩ
R <sub>DS(on)</sub>	Drain-to-Source On-Resistance	V <sub>GS</sub> = 10V 2.3		mΩ
V <sub>GS(th)</sub>	Threshold Voltage	2.5		V

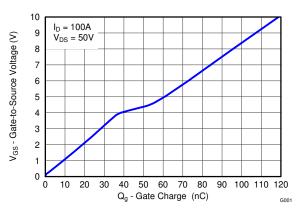
### **Ordering Information**

Device Package		Media	Qty	Ship
CSD19536KCS	TO-220 Plastic Package	Tube	50	Tube

#### **Absolute Maximum Ratings**

T <sub>A</sub> = 2	25°C	VALUE	UNIT	
V <sub>DS</sub>	Drain-to-Source Voltage	100	V	
V <sub>GS</sub>	Gate-to-Source Voltage	±20	V	
	Continuous Drain Current (Package limited)	150		
I <sub>D</sub>	Continuous Drain Current (Silicon limited), T <sub>C</sub> = 25°C	259	A	
	Continuous Drain Current (Silicon limited), T <sub>C</sub> = 100°C	183		
I <sub>DM</sub>	Pulsed Drain Current (1)	400	Α	
P <sub>D</sub>	Power Dissipation	375	W	
T <sub>J</sub> , T <sub>stg</sub>	Operating Junction and Storage Temperature Range	-55 to 175	°C	
E <sub>AS</sub>	Avalanche Energy, single pulse $I_D$ = 127A, L = 0.1mH, $R_G$ = 25 $\Omega$	806	mJ	

### Max R<sub>θJC</sub> = 0.4°C/W, pulse duration ≤100μs, duty cycle ≤1%



**Gate Charge** 



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## 4 Specifications

## **4.1 Electrical Characteristics**

(T<sub>A</sub> = 25°C unless otherwise stated)

	PARAMETER	TEST CONDITIONS	MIN TYP	MAX	UNIT
STATIC	CHARACTERISTICS		<u>'</u>		
BV <sub>DSS</sub>	Drain-to-Source Voltage	V <sub>GS</sub> = 0V, I <sub>D</sub> = 250μA	100		V
I <sub>DSS</sub>	Drain-to-Source Leakage Current	V <sub>GS</sub> = 0V, V <sub>DS</sub> = 80V		1	μΑ
I <sub>GSS</sub>	Gate-to-Source Leakage Current	V <sub>DS</sub> = 0V, V <sub>GS</sub> = 20V		100	nA
V <sub>GS(th)</sub>	Gate-to-Source Threshold Voltage	$V_{DS} = V_{GS}$ , $I_D = 250\mu A$	2.1 2.5	3.2	V
Б	Drain to Source On Decistance	V <sub>GS</sub> = 6V, I <sub>D</sub> = 100A	2.5	3.2	mΩ
R <sub>DS(on)</sub>	Drain-to-Source On-Resistance	V <sub>GS</sub> = 10V, I <sub>D</sub> = 100A	2.3	2.7	mΩ
g <sub>fs</sub>	Transconductance	V <sub>DS</sub> = 10V, I <sub>D</sub> = 100A	307		S
DYNAM	IC CHARACTERISTICS		-	. '	
C <sub>iss</sub>	Input Capacitance		9250	12000	pF
C <sub>oss</sub>	Output Capacitance	$V_{GS} = 0V, V_{DS} = 50V, f = 1MHz$	1820	2370	pF
C <sub>rss</sub>	Reverse Transfer Capacitance		47	61	pF
$R_G$	Series Gate Resistance		1.4	2.8	Ω
Q <sub>g</sub>	Gate Charge Total (10V)		118	153	nC
Q <sub>gd</sub>	Gate Charge Gate to Drain	V - 50V L - 400A	17		nC
Q <sub>gs</sub>	Gate Charge Gate to Source	$V_{DS} = 50V, I_{D} = 100A$	37		nC
Q <sub>g(th)</sub>	Gate Charge at V <sub>th</sub>		24		nC
Q <sub>oss</sub>	Output Charge	V <sub>DS</sub> = 50V, V <sub>GS</sub> = 0V	335		nC
t <sub>d(on)</sub>	Turn On Delay Time		14		ns
t <sub>r</sub>	Rise Time	V <sub>DS</sub> = 50V, V <sub>GS</sub> = 10V,	8		ns
t <sub>d(off)</sub>	Turn Off Delay Time	$I_{DS} = 100A$ , $R_G = 0\Omega$	38		ns
t <sub>f</sub>	Fall Time		5		ns
DIODE (	CHARACTERISTICS	,		I	
$V_{SD}$	Diode Forward Voltage	I <sub>SD</sub> = 100A, V <sub>GS</sub> = 0V	0.9	1.1	V
Q <sub>rr</sub>	Reverse Recovery Charge	V <sub>DS</sub> = 50V, I <sub>F</sub> = 100A,	548		nC
t <sub>rr</sub>	Reverse Recovery Time	di/dt = 300A/µs	110		ns

## **4.2 Thermal Information**

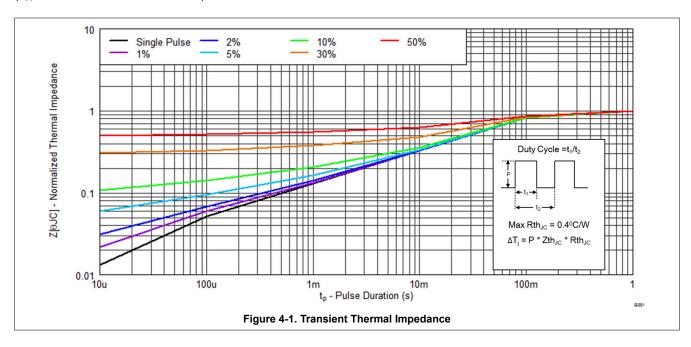
(T<sub>A</sub> = 25°C unless otherwise stated)

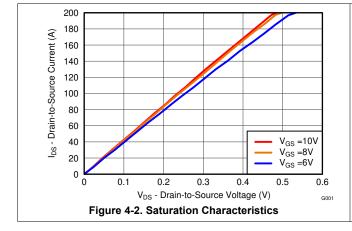
	THERMAL METRIC				UNIT
$R_{\theta JC}$	Junction-to-Case Thermal Resistance			0.4	°C/W
$R_{\theta JA}$	Junction-to-Ambient Thermal Resistance			62	C/VV

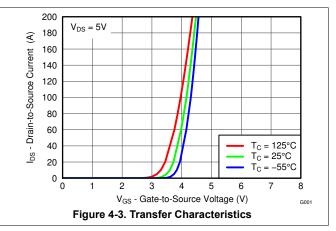


# **4.3 Typical MOSFET Characteristics**

(T<sub>A</sub> = 25°C unless otherwise stated)





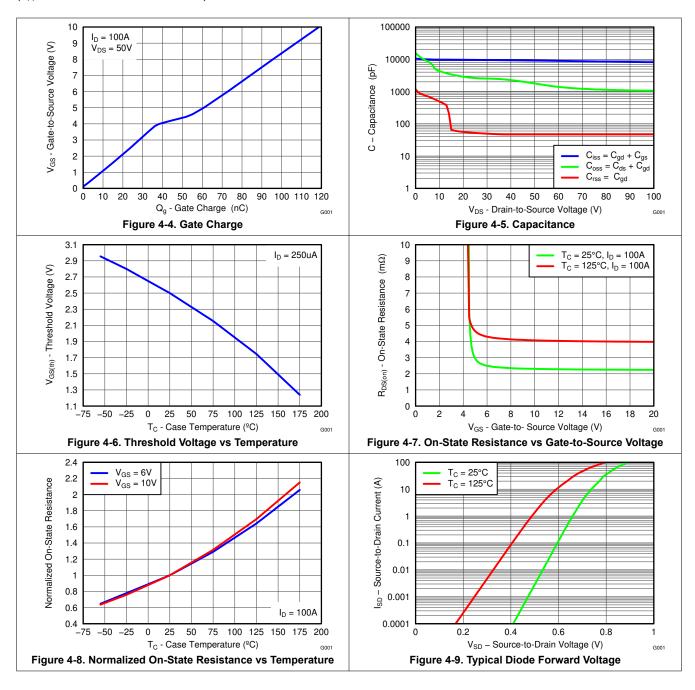


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## 4.3 Typical MOSFET Characteristics (continued)

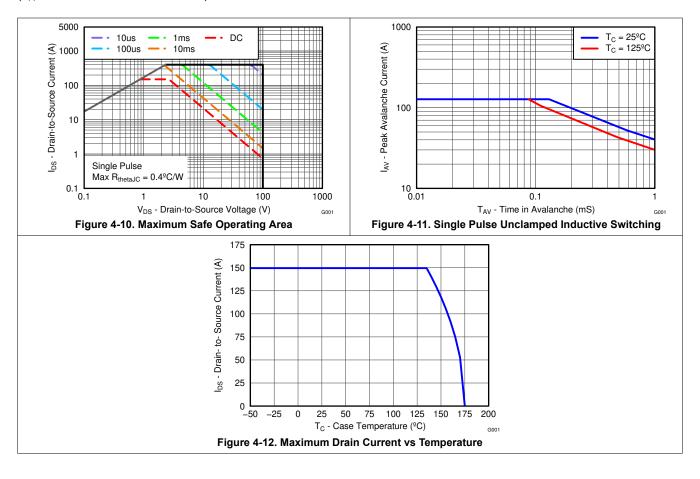
(T<sub>A</sub> = 25°C unless otherwise stated)





## 4.3 Typical MOSFET Characteristics (continued)

(T<sub>A</sub> = 25°C unless otherwise stated)





## 5 Device and Documentation Support

## 5.1 Receiving Notification of Documentation Updates

To receive notification of documentation updates, navigate to the device product folder on ti.com. Click on *Notifications* to register and receive a weekly digest of any product information that has changed. For change details, review the revision history included in any revised document.

### **5.2 Support Resources**

TI E2E<sup>™</sup> support forums are an engineer's go-to source for fast, verified answers and design help — straight from the experts. Search existing answers or ask your own question to get the quick design help you need.

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#### 5.3 Trademarks

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### 5.4 Electrostatic Discharge Caution



This integrated circuit can be damaged by ESD. Texas Instruments recommends that all integrated circuits be handled with appropriate precautions. Failure to observe proper handling and installation procedures can cause damage.

ESD damage can range from subtle performance degradation to complete device failure. Precision integrated circuits may be more susceptible to damage because very small parametric changes could cause the device not to meet its published specifications.

## 5.5 Glossary

TI Glossary

This glossary lists and explains terms, acronyms, and definitions.

#### 6 Revision History

NOTE: Page numbers for previous revisions may differ from page numbers in the current version.

Changes from Revision B (October 2014) to Revision C (May 2024)	Page
Updated the numbering format for tables, figures, and cross-references throughout the	document1
Changes from Revision A (April 2014) to Revision B (April 2014)	Page
Updated Pulsed Drain Current conditions	1
Updated the SOA in Figure 4-10	4
Changes from Revision * (January 2014) to Revision A (April 2014)	Page
Increased pulsed current rating to 400A	
Updated SOA curve	



## 7 Mechanical, Packaging, and Orderable Information

The following pages include mechanical packaging and orderable information. This information is the most current data available for the designated devices. This data is subject to change without notice and revision of this document. For browser-based versions of this data sheet, refer to the left-hand navigation.

www.ti.com 8-Nov-2025

#### PACKAGING INFORMATION

Orderable part number	Status	Material type	Package   Pins	Package qty   Carrier	<b>RoHS</b> (3)	Lead finish/ Ball material	MSL rating/ Peak reflow	Op temp (°C)	Part marking (6)
CSD19536KCS	Active	Production	TO-220 (KCS)   3	50   TUBE	ROHS Exempt	SN	N/A for Pkg Type	-55 to 175	CSD19536KCS
CSD19536KCS.B	Active	Production	TO-220 (KCS)   3	50   TUBE	ROHS Exempt	SN	N/A for Pkg Type	-55 to 175	CSD19536KCS

<sup>(1)</sup> Status: For more details on status, see our product life cycle.

Multiple part markings will be inside parentheses. Only one part marking contained in parentheses and separated by a "~" will appear on a part. If a line is indented then it is a continuation of the previous line and the two combined represent the entire part marking for that device.

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<sup>(3)</sup> RoHS values: Yes, No, RoHS Exempt. See the TI RoHS Statement for additional information and value definition.

<sup>(4)</sup> Lead finish/Ball material: Parts may have multiple material finish options. Finish options are separated by a vertical ruled line. Lead finish/Ball material values may wrap to two lines if the finish value exceeds the maximum column width.

<sup>(5)</sup> MSL rating/Peak reflow: The moisture sensitivity level ratings and peak solder (reflow) temperatures. In the event that a part has multiple moisture sensitivity ratings, only the lowest level per JEDEC standards is shown. Refer to the shipping label for the actual reflow temperature that will be used to mount the part to the printed circuit board.

<sup>(6)</sup> Part marking: There may be an additional marking, which relates to the logo, the lot trace code information, or the environmental category of the part.

# **PACKAGE MATERIALS INFORMATION**

www.ti.com 23-May-2025

### **TUBE**



\*All dimensions are nominal

Device	Package Name	Package Type	Pins	SPQ	L (mm)	W (mm)	T (µm)	B (mm)
CSD19536KCS	KCS	TO-220	3	50	532	34.1	700	9.6
CSD19536KCS	KCS	TO-220	3	50	534.5	33	7000	3.4
CSD19536KCS.B	KCS	TO-220	3	50	534.5	33	7000	3.4
CSD19536KCS.B	KCS	TO-220	3	50	532	34.1	700	9.6



TO-220



#### NOTES:

- 1. Dimensions are in millimeters. Any dimension in brackets or parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.

  2. This drawing is subject to change without notice.

  3. Reference JEDEC registration TO-220.



TO-220



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